

SILICON CURRENT REGULATOR DIODE

DESCRIPTION:

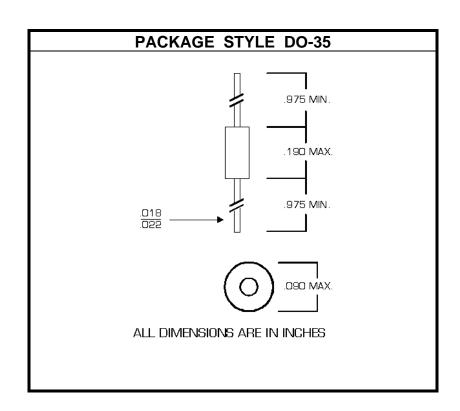
The **1N5290** is Silicon Constant Current Diode Designed for General Purpose Power Supply and Signal Processing Applications.

FEATURES INCLUDE:

- $I_P = 470 \mu A$ Nominal
- $Z_T = 2.70 \text{ M}\Omega$ Minimum
- Hermetic DO-35 Package

MAXIMUM RATINGS

Pov	100 V				
P _{DISS}	600 mW @ $T_C = 75$ °C				
TJ	-55 °C to +200 °C				
T _{STG}	-55 °C to +200 °C				
θ _{JC}	210 °C/W				



CHARACTERISTICS T_c = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I _P	$V_T = 25 \text{ V}$	423		517	μΑ
Z _T	$V_T = 25 \text{ V}$	2.70			mΩ
Z _K	$V_{K} = 6.0 \text{ V}$	750			ΚΩ
V _L	Ι _L = 338 μΑ			1.05	٧